

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: YAMAZAKI, et al.

Application No.: TBD

Filed: August 13, 2003

For: FABRICATION METHOD FOR SEMICONDUCTOR INTEGRATED
CIRCUIT DEVICE

Expected
Group: 2822

Expected
Examiner: S. Meier

**INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR § 1.97 AND § 1.98**

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

August 13, 2003

Sir:

Pursuant to Applicants' duty of disclosure, enclosed please find a List, on a form substantially equivalent to Form PTO-1449, of documents cited in connection with prior applications of the above-identified application, that is, Application No. 09/810,577, filed March 19, 2001, and Application No. 09/811,589, filed March 20, 2001.

Since the above-identified prior Application No. 09/810,577 and No. 09/811,589 are being relied upon under 35 USC § 120 in the present application, copies of the listed documents are not enclosed. See 37 CFR § 1.98(d).

This Information Disclosure Statement is being submitted concurrently with the filing of the above-identified application. Accordingly, requirements of

37 CFR 1.97(b) are clearly satisfied.

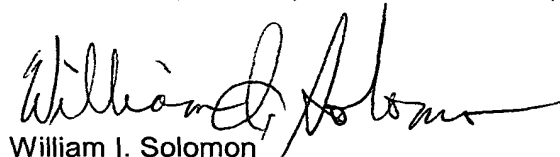
Of the documents on the enclosed List, please note that the listed Japanese patent document, and the "OTHER DOCUMENTS" listed, are discussed in the specification of the above-identified application (see page 1 of this specification). Clearly, requirements of 37 CFR 1.98(a)(3) are satisfied, in connection with all documents on the enclosed List

In view of all of the foregoing, it is respectfully submitted that all applicable requirements of 37 CFR § 1.97 and § 1.98 have been satisfied, in connection with all documents on the enclosed List. Accordingly, consideration of the listed documents, upon examination of the above-identified application, is respectfully requested.

To the extent necessary, Applicants petition for an extension of time under 37 CFR § 1.136. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to the Deposit Account No. 01-2135 (Case No. 501.39812VV2) and please credit any excess fees to such Deposit Account.

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP

A handwritten signature in black ink, appearing to read "William I. Solomon", with a long horizontal flourish extending to the right.

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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DKT. NO. 501.39812VV2	SERIAL NO. TBD
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT YAMAZAKI, et al.	
		FILING DATE August 13, 2003	EXPECTED GROUP 2822

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
	AA	6,200,866	3-2001	Ma, et al.		
	AB	6,319,840	11-2001	Costrini, et al.		
	AC	6,335,266	1-2002	Kitahara, et al.		
	AD	6,344,383	2-2002	Berry, et al.		
	AE	6,348,420	2-2002	Raaijmakers, et al.		
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AM	11330463	11-1999	Japan			
	AN	2805924	9-2001	France			
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	AU	Polysilicon-Germanium Gate Patterning Studies in a High Density Plasma Helicon Souce, 1997 American Vacuum Society, pp. 1874-1880
	AV	Germanium Etching in High Density Plasmas for 0.18 PM Complementary Metal-Oxide-Semiconductor Gate Patterning Applications, 1998 American Vacuum Society, pp. 1833-1840
	AW	
	AX	
	AY	
	AZ	
Examiner		Date Considered